

FY8AAJ-03F

High-Speed Switching Use
Nch Power MOS FET

REJ03G0280-0100

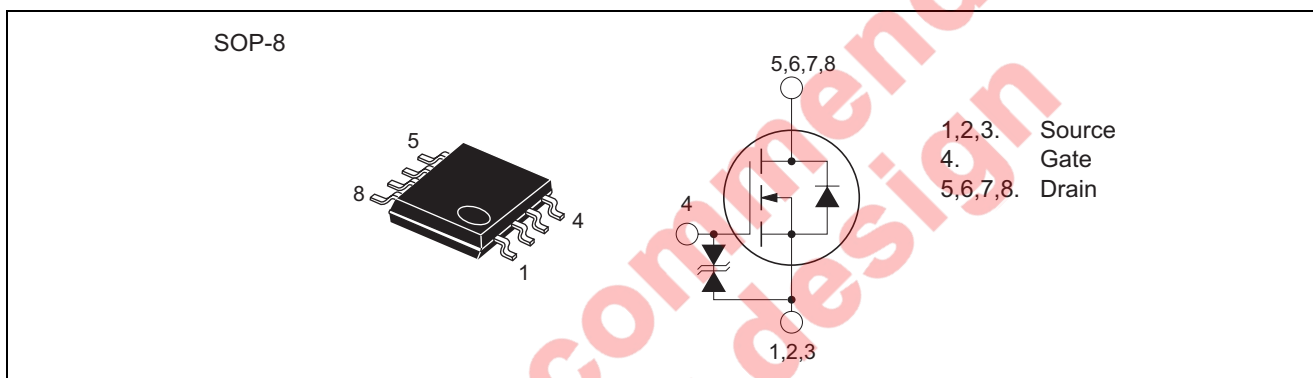
Rev.1.00

Aug.20.2004

Features

- Drive voltage : 4 V
- V_{DSS} : 30 V
- $I_{DS(ON)(max)}$: 28 mΩ
- I_D : 8 A

Outline



Applications

Motor control, lamp control, solenoid control, DC-DC converters, etc.

Maximum Ratings

($T_c = 25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V_{DSS}	30	V	$V_{GS} = 0\text{ V}$
Gate-source voltage	V_{GSS}	± 20	V	$V_{DS} = 0\text{ V}$
Drain current	I_D	8	A	
Drain current (Pulsed)	I_{DM}	56	A	
Avalanche current (Pulsed)	I_{DA}	8	A	$L = 10\text{ }\mu\text{H}$
Source current	I_S	1.5	A	
Source current (Pulsed)	I_{SM}	6.0	A	
Maximum power dissipation	P_D	1.7	W	
Channel temperature	T_{ch}	-55 to $+150$	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to $+150$	$^\circ\text{C}$	
Mass	—	0.07	g	Typical value

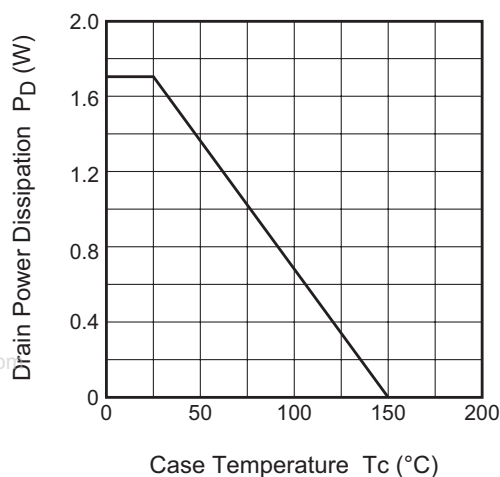
Electrical Characteristics

(Tch = 25°C)

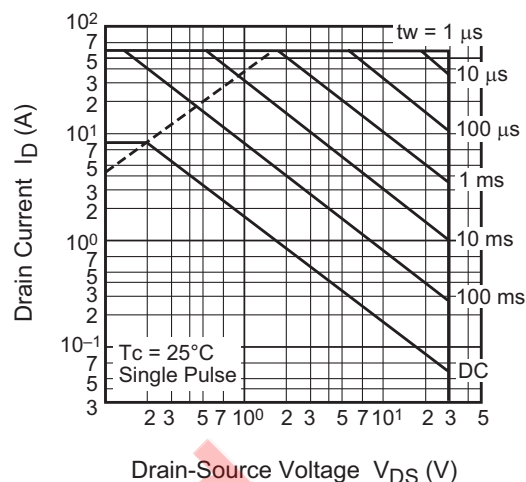
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 1 \text{ mA}$, $V_{GS} = 0 \text{ V}$
Gate-source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0 \text{ V}$
Drain-source leakage current	I_{DSS}	—	—	0.1	mA	$V_{DS} = 30 \text{ V}$, $V_{GS} = 0 \text{ V}$
Gate-source leakage current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$
Gate-source threshold voltage	$V_{GS(th)}$	1.0	1.5	2.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Drain-source on-state resistance	$r_{DS(ON)}$	—	22	28	$\text{m}\Omega$	$I_D = 8 \text{ A}$, $V_{GS} = 10 \text{ V}$
Drain-source on-state resistance	$r_{DS(ON)}$	—	31	43	$\text{m}\Omega$	$I_D = 4 \text{ A}$, $V_{GS} = 4.5 \text{ V}$
Drain-source on-state resistance	$r_{DS(ON)}$	—	35	50	$\text{m}\Omega$	$I_D = 4 \text{ A}$, $V_{GS} = 4 \text{ V}$
Drain-source on-state voltage	$V_{DS(ON)}$	—	0.176	0.224	V	$I_D = 8 \text{ A}$, $V_{GS} = 10 \text{ V}$
Forward transfer admittance	$ y_{fs} $	—	13	—	S	$I_D = 8 \text{ A}$, $V_{DS} = 10 \text{ V}$
Input capacitance	C_{iss}	—	600	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	200	—	pF	
Reverse transfer capacitance	C_{rss}	—	90	—	pF	
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	$V_{DD} = 15 \text{ V}$, $I_D = 4 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_G = 5 \text{ }\Omega$
Rise time	t_r	—	15	—	ns	
Turn-off delay time	$t_{d(off)}$	—	40	—	ns	
Fall time	t_f	—	6.5	—	ns	
Total gate charge	Q_g	—	13.8	—	nC	$V_{DD} = 15 \text{ V}$, $I_D = 8 \text{ A}$, $V_{GS} = 10 \text{ V}$
Gate-source charge	Q_{gs}	—	1.6	—	nC	
Gate-drain charge	Q_{gd}	—	3.5	—	nC	
Source-drain voltage	V_{SD}	—	0.75	1.10	V	$I_S = 1.5 \text{ A}$, $V_{GS} = 0 \text{ V}$
Thermal resistance	$R_{th(ch-a)}$	—	—	73.5	$^{\circ}\text{C/W}$	Channel to air
Reverse recovery time	t_{rr}	—	40	—	ns	$I_S = 1.5 \text{ A}$, $\text{dis}/\text{dt} = -50 \text{ A}/\mu\text{s}$

Performance Curves

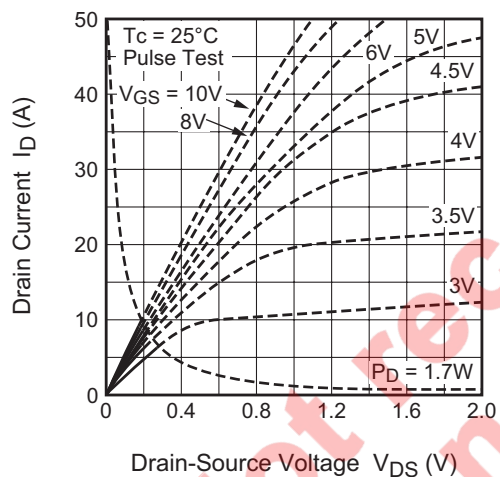
Drain Power Dissipation Derating Curve



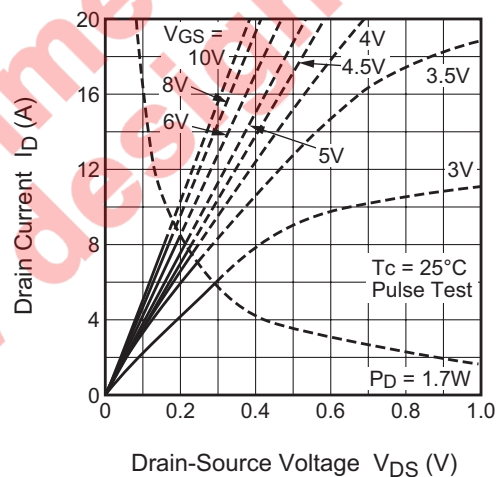
Maximum Safe Operating Area



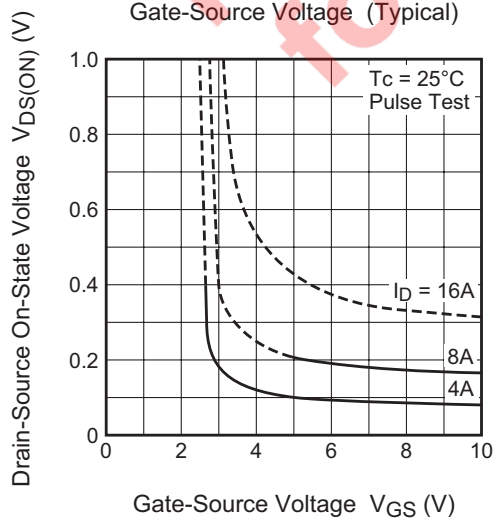
Output Characteristics (Typical)



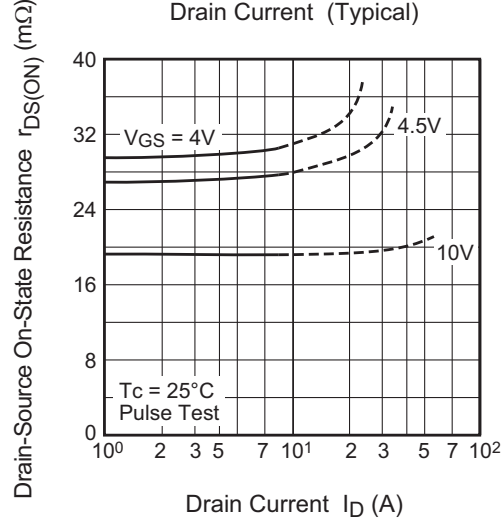
Output Characteristics (Typical)



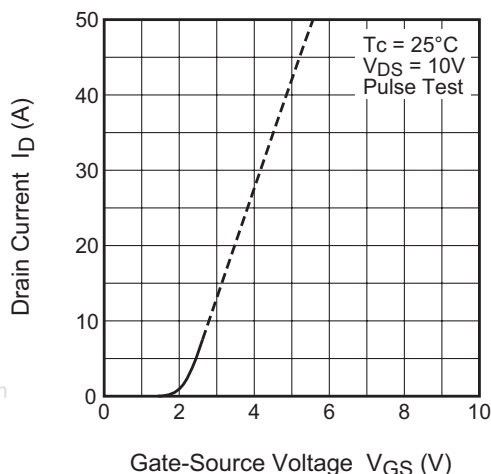
On-State Voltage vs. Gate-Source Voltage (Typical)



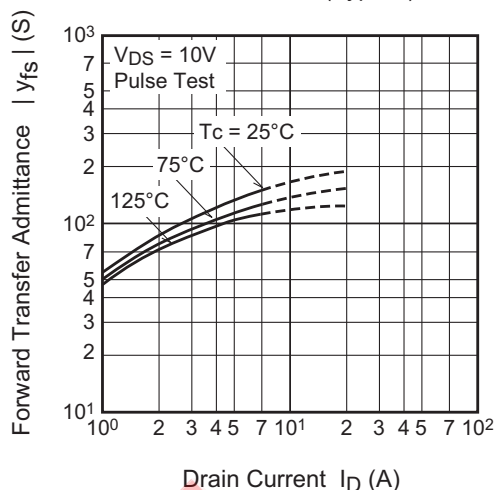
On-State Resistance vs. Drain Current (Typical)



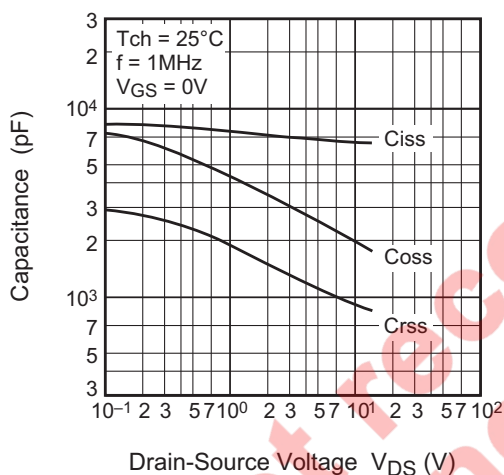
Transfer Characteristics (Typical)



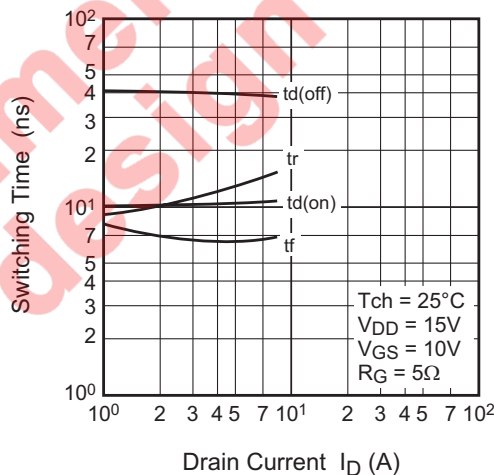
Forward Transfer Admittance vs. Drain Current (Typical)



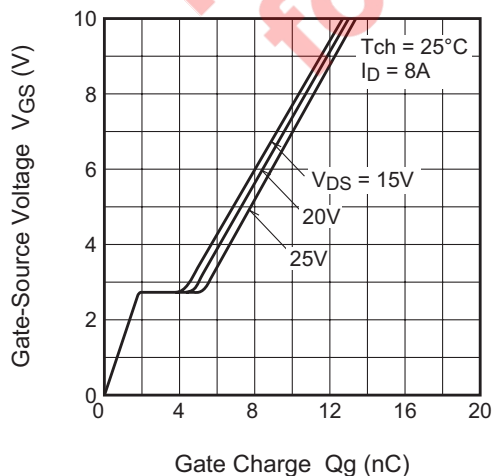
Capacitance vs. Drain-Source Voltage (Typical)



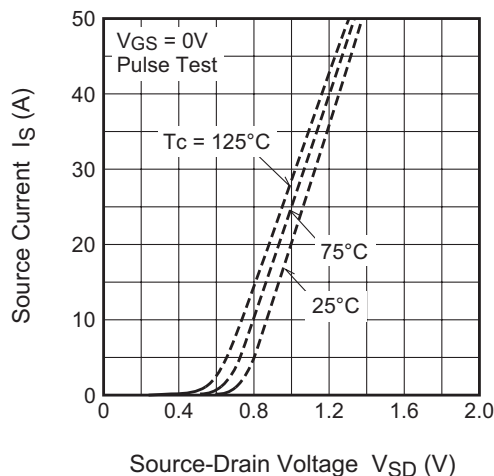
Switching Characteristics (Typical)



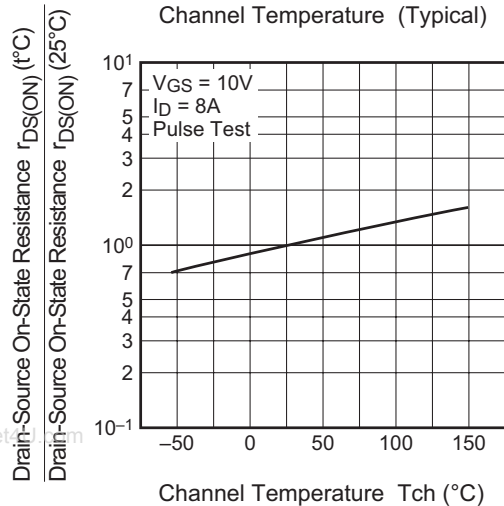
Gate-Source Voltage vs. Gate Charge (Typical)



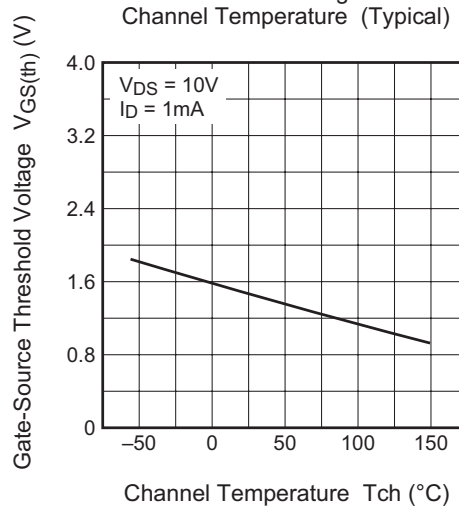
Source-Drain Diode Forward Characteristics (Typical)



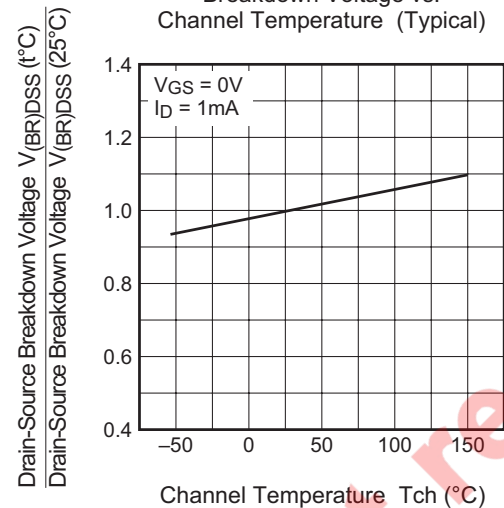
On-State Resistance vs.
Channel Temperature (Typical)



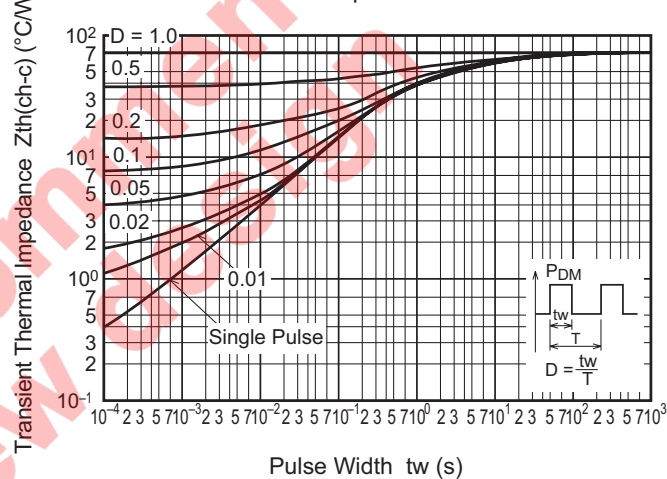
Threshold Voltage vs.
Channel Temperature (Typical)



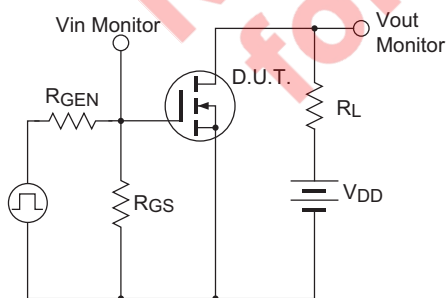
Breakdown Voltage vs.
Channel Temperature (Typical)



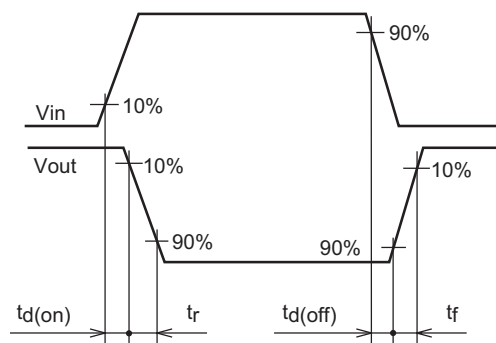
Transient Thermal Impedance Characteristics



Switching Time Measurement Circuit



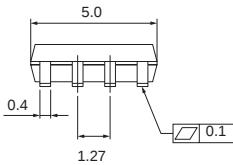
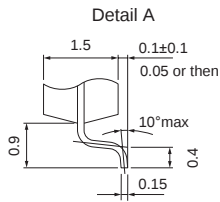
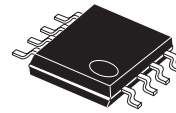
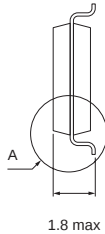
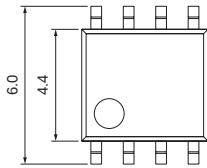
Switching Waveform



Package Dimensions

8P2S-B(SOP-8)

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
—	Conforms	0.07	Cu alloy



Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

Symbol	Dimension in Millimeters		
	Min	Typ	Max
A	—	—	—
A ₁	—	—	—
A ₂	—	—	—
b	—	—	—
D	—	—	—
E	—	—	—
e	—	—	—
x	—	—	—
y	—	—	—
y ₁	—	—	—
ZD	—	—	—
ZE	—	—	—

Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	FY8AAJ-03F-T13
Surface-mounted type	Plastic Magazine (Tube)	100	Type name	FY8AAJ-03F

Note : Please confirm the specification about the shipping in detail.

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